

MOSFETs Silicon N-channel MOS (U-MOS<sup>VI</sup>-H)

# TPN13008NH

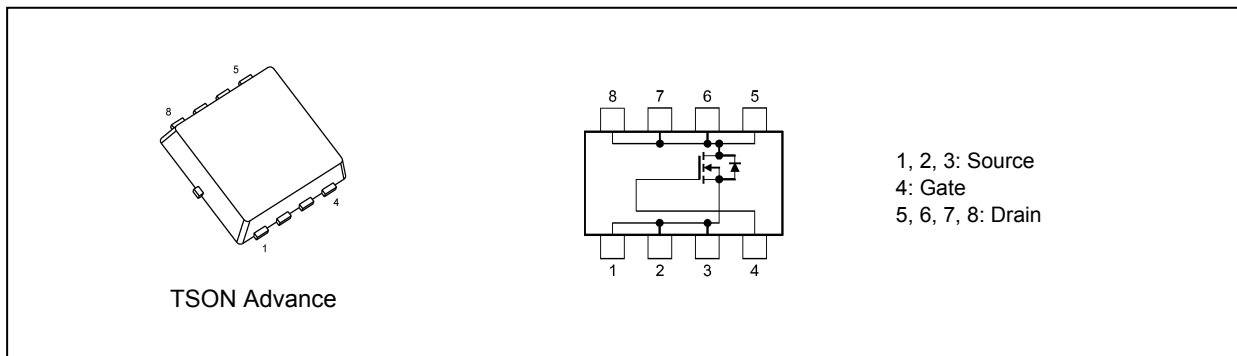
## 1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

## 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 6.7 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 10.8 \text{ m}\Omega \text{ (typ.)}$  ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max)}$  ( $V_{DS} = 80 \text{ V}$ )
- (6) Enhancement mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 0.2 \text{ mA}$ )

## 3. Packaging and Internal Circuit



Start of commercial production

2012-08

## 4. Absolute Maximum Ratings (Note) ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	80	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current (DC) (Silicon limit) (Note 1), (Note 2)	$I_D$	40	A
Drain current (DC) ( $T_c = 25\text{ }^\circ\text{C}$ ) (Note 1)	$I_D$	18	
Drain current (pulsed) ( $t = 1\text{ ms}$ ) (Note 1)	$I_{DP}$	98	A
Power dissipation ( $T_c = 25\text{ }^\circ\text{C}$ )	$P_D$	42	W
Power dissipation ( $t = 10\text{ s}$ ) (Note 3)	$P_D$	1.9	W
Power dissipation ( $t = 10\text{ s}$ ) (Note 4)	$P_D$	0.7	W
Single-pulse avalanche energy (Note 5)	$E_{AS}$	114	mJ
Avalanche current	$I_{AR}$	18	A
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ( $T_c = 25\text{ }^\circ\text{C}$ )	$R_{th(ch-c)}$	2.97	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 3)	$R_{th(ch-a)}$	65.7	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 4)	$R_{th(ch-a)}$	178	

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD} = 60\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (initial),  $L = 0.3\text{ mH}$ ,  $R_G = 1.0\text{ }\Omega$ ,  $I_{AR} = 18\text{ A}$

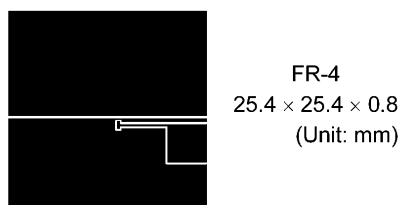


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

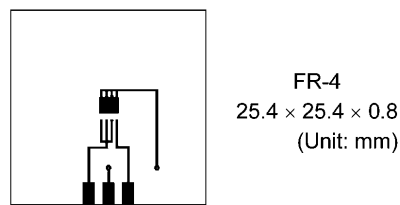


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

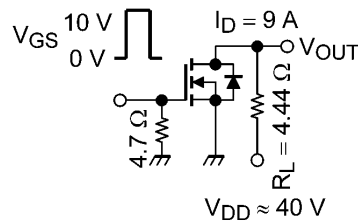
## 6. Electrical Characteristics

### 6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 0.1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	80	—	—	V
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	60	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 0.2\text{ mA}$	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	—	10.8	13.3	$\text{m}\Omega$

### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1230	1600	$\mu\text{F}$
Reverse transfer capacitance	$C_{rss}$		—	20	50	
Output capacitance	$C_{oss}$		—	290	—	
Gate resistance	$r_g$	—	—	0.9	1.4	$\Omega$
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	4.5	—	ns
Switching time (turn-on time)	$t_{on}$		—	14	—	
Switching time (fall time)	$t_f$		—	5.0	—	
Switching time (turn-off time)	$t_{off}$		—	18	—	



Duty  $\leq 1\%$ ,  $t_w = 10\text{ }\mu\text{s}$

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	18	—	nC
Gate-source charge 1	$Q_{gs1}$		—	6.5	—	
Gate-drain charge	$Q_{gd}$		—	4.0	—	
Gate switch charge	$Q_{sw}$		—	6.7	—	

### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 6)	$I_{DRP}$	—	—	—	98	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = 18\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

Note 6: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

## 7. Marking

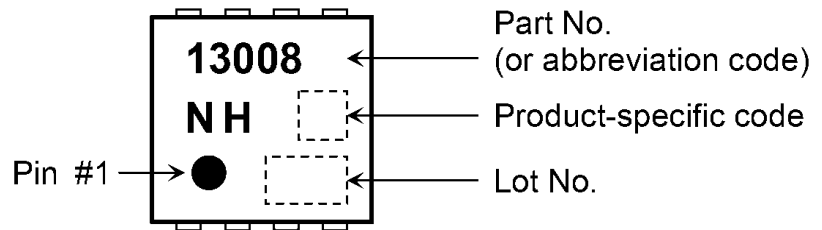


Fig. 7.1 Marking

## 8. Characteristics Curves (Note)

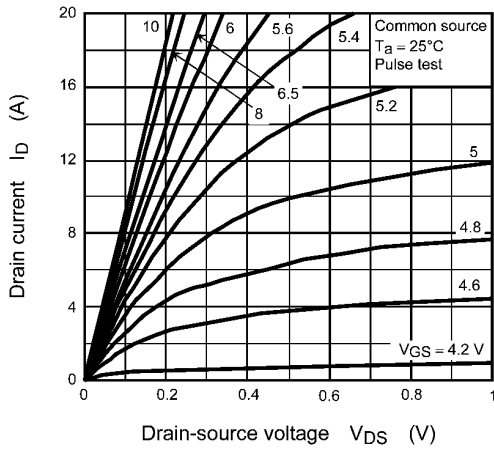


Fig. 8.1  $I_D - V_{DS}$

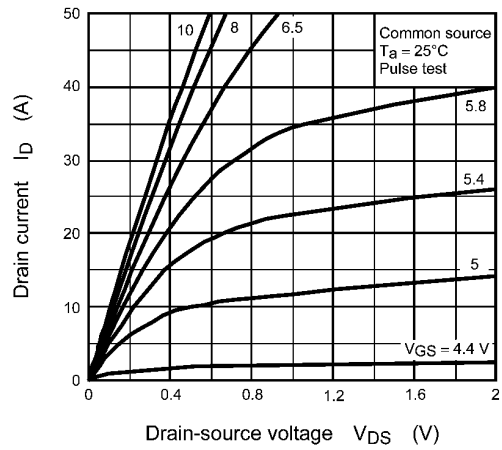


Fig. 8.2  $I_D - V_{DS}$

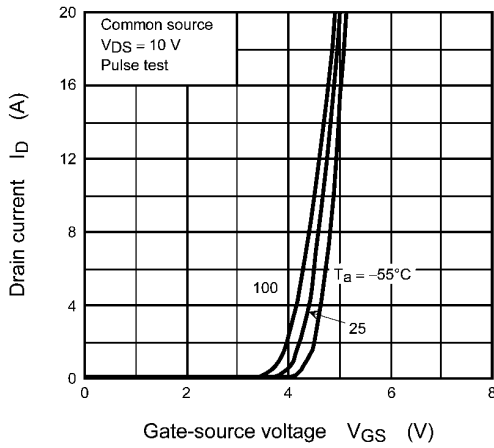


Fig. 8.3  $I_D - V_{GS}$

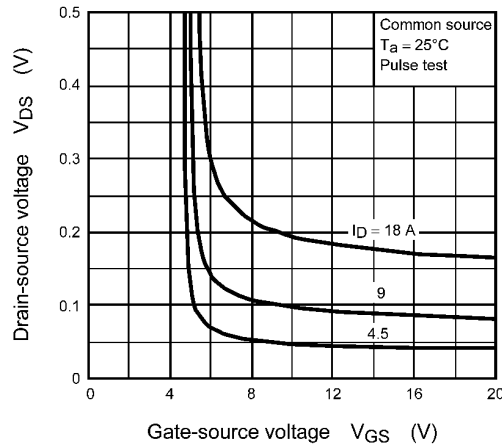


Fig. 8.4  $V_{DS} - V_{GS}$

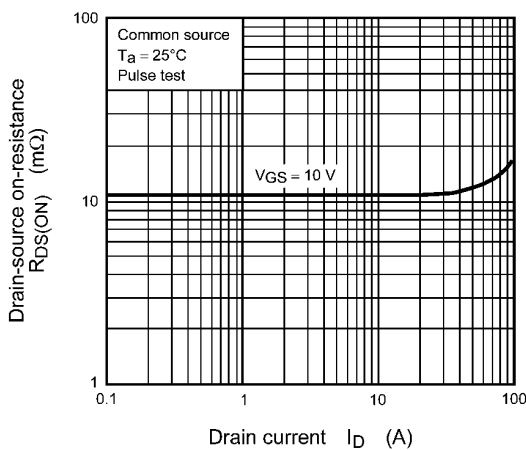


Fig. 8.5  $R_{DS(ON)} - I_D$

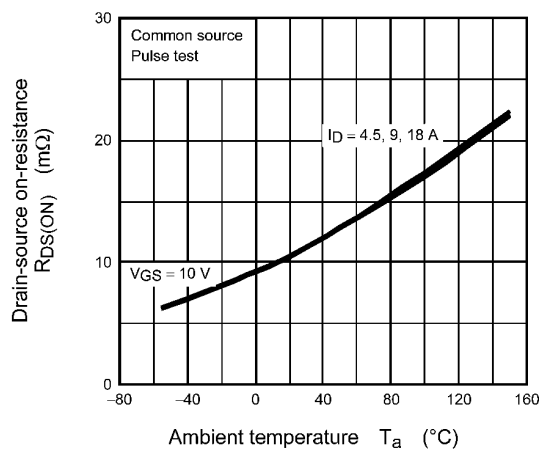
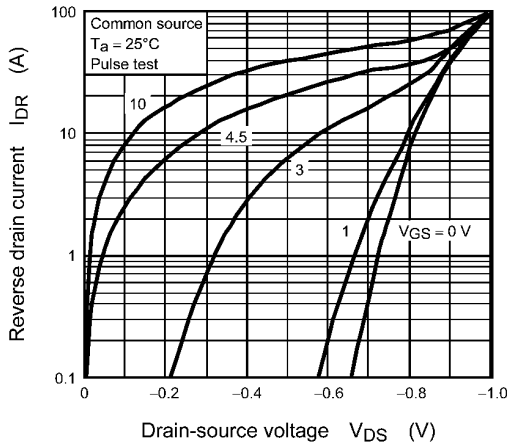
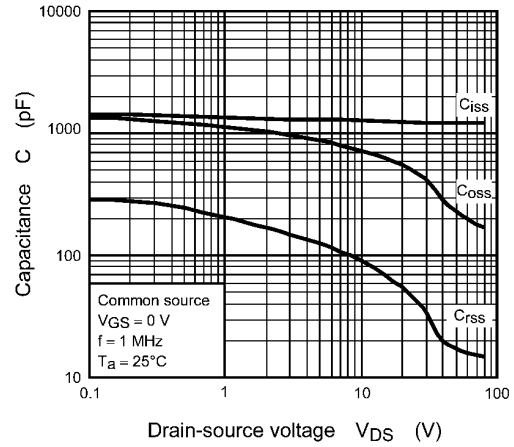


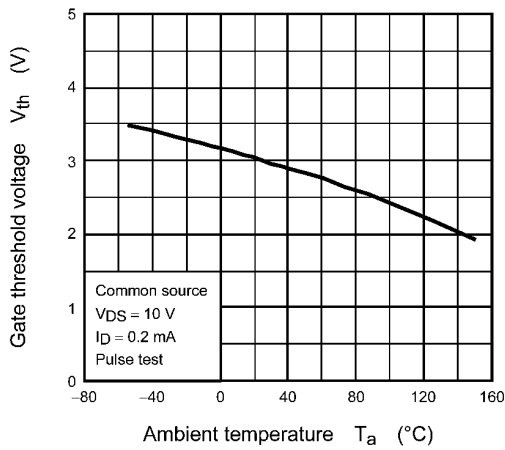
Fig. 8.6  $R_{DS(ON)} - T_a$



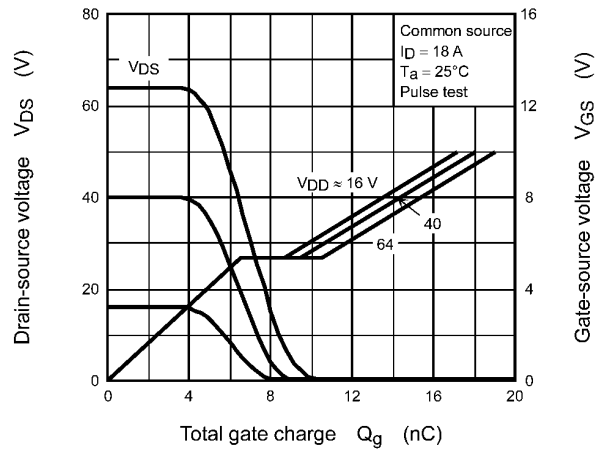
**Fig. 8.7  $I_{DR} - V_{DS}$**



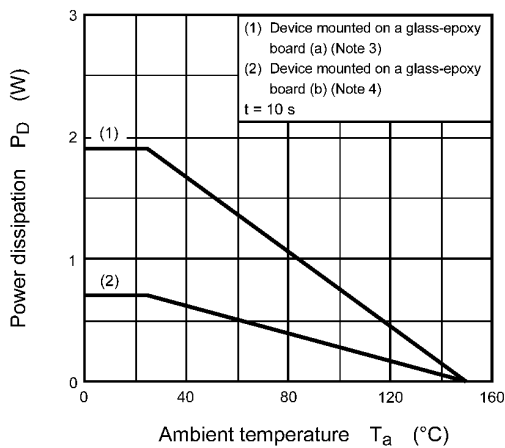
**Fig. 8.8 Capacitance -  $V_{DS}$**



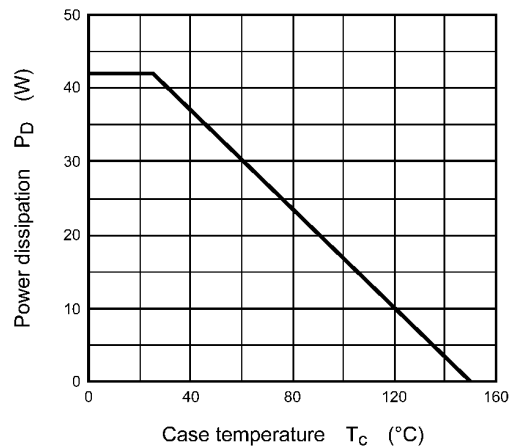
**Fig. 8.9  $V_{th} - T_a$**



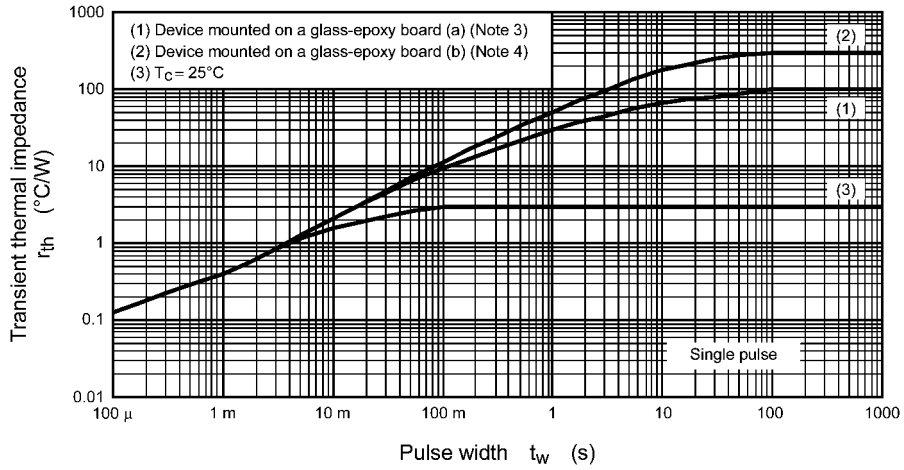
**Fig. 8.10 Dynamic Input/Output Characteristics**



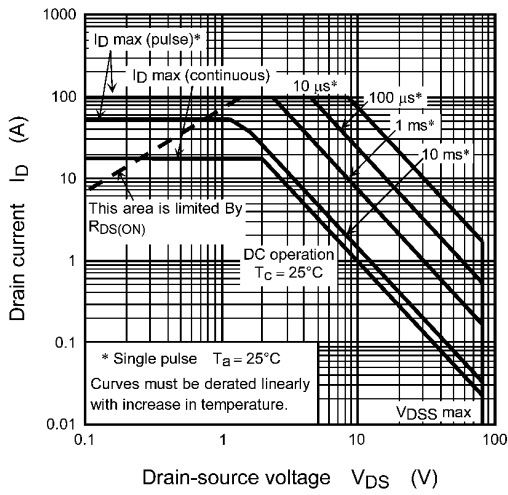
**Fig. 8.11  $P_D - T_a$   
(Guaranteed Maximum)**



**Fig. 8.12  $P_D - T_c$   
(Guaranteed Maximum)**



**Fig. 8.13  $r_{th} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.14 Safe Operating Area**  
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance



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